

TOSHIBA GTR MODULE SILICON N CHANNEL IGBT

MG100J2YS50

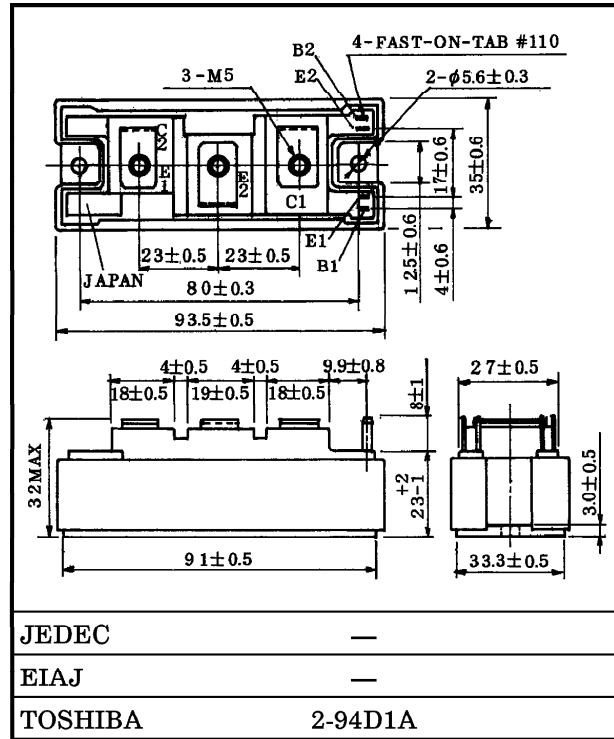
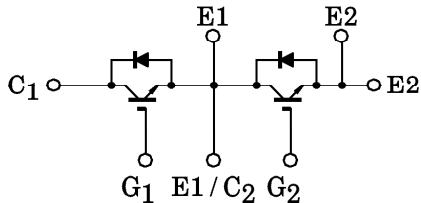
HIGH POWER SWITCHING APPLICATIONS.

Unit in mm

MOTOR CONTROL APPLICATIONS.

- The Electrodes are Isolated from Case.
- High Input Impedance.
- Includes a Complete Half Bridge in One Package.
- Enhancement-Mode.
- High Speed : $t_f=0.30\mu s$ (Max.) ($I_C=100A$)
 $t_{rr}=0.15\mu s$ (Max.) ($I_F=100A$)
- Low Saturation Voltage
: $V_{CE(sat)}=2.70V$ (Max.) ($I_C=100A$)

EQUIVALENT CIRCUIT



Weight : 202g (TYP.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V _{CES}	600	V
Gate-Emitter Voltage	V _{GES}	±20	V
Collector Current	DC	I _C	100
	1ms	I _{CP}	200
Forward Current	DC	I _F	100
	1ms	I _{FM}	200
Collector Power Dissipation (T _c = 25°C)	P _C	450	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-40~125	°C
Isolation Voltage	V _{Isol}	2500 (AC 1 min.)	V
Screw Torque (Terminal/Mounting)	—	3 / 3	N·m

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-off Current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE} (off)$	$I_C = 10mA, V_{CE} = 5V$	5.0	7.0	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 100A, V_{GE} = 15V$	—	2.10	2.70	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	9000	—	pF
Switching Time	Turn-on Delay Time	$t_d (on)$	Inductive Load $V_{CC} = 300V$ $I_C = 100A$ $V_{GE} = \pm 15V$ $R_G = 13\Omega$ (Note 1)	—	0.08	0.16	μs
	Rise Time	t_r		—	0.12	0.24	
	Turn-on Time	t_{on}		—	0.40	0.80	
	Turn-off Delay Time	$t_d (off)$		—	0.20	0.40	
	Fall Time	t_f		—	0.15	0.30	
	Turn-off Time	t_{off}		—	0.50	1.00	
Forward Voltage		V_F	$I_F = 100A, V_{GE} = 0$	—	2.30	3.00	V
Reverse Recovery Time		t_{rr}	$I_F = 100A, V_{GE} = -10V$ $di / dt = 100A / \mu s$	—	0.08	0.15	μs
Thermal Resistance		$R_{th} (j-c)$	Transistor Stage	—	—	0.28	$^{\circ}C / W$
			Diode Stage	—	—	0.69	

Note 1 Switching Time Test Circuit & Timing Chart

